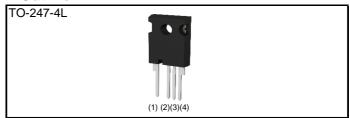
SCT3030ARHR

Automotive Grade N-channel SiC power MOSFET

Datasheet

V_{DSS}	650V
R _{DS(on)} (Typ.)	30mΩ
I _D *1	70A
P_{D}	262W

Outline



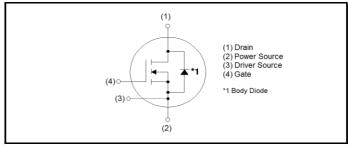
Features

- 1) Qualified to AEC-Q101
- 2) Low on-resistance
- 3) Fast switching speed
- 4) Fast reverse recovery
- 5) Easy to parallel
- 6) Simple to drive
- 7) Pb-free lead plating; RoHS compliant

Application

- Automobile
- Switch mode power supplies

●Inner circuit



Please note Driver Source and Power Source are not exchangeable. Their exchange might lead to malfunction.

Packaging specifications

	Packing	Tube
	Reel size (mm)	-
Typo	Tape width (mm)	-
Type	Basic ordering unit (pcs)	30
	Taping code	C15
	Marking	SCT3030AR

● **Absolute maximum ratings** (T_{vj} = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DSS}	650	V
Continuous Drain current	T _c = 25°C	I _D *1	70	А
Continuous Drain current	T _c = 100°C	I _D *1	49	А
Pulsed Drain current (T _c = 25°C)		I _{D,pulse} *2	I _{D,pulse} *2 175	
Gate - Source voltage (DC)		V_{GSS}	-4 to +22	V
Gate - Source surge voltage (t _{surge} < 300ns)		V _{GSS_surge} *3	-4 to +26	V
Recommended drive voltage		V _{GS_op} *4	0 / +18	V
Virtual Junction temperature		T_{vj}	175	°C
Range of storage temperature		T _{stg}	-55 to +175	°C

●Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

Doromotor	Symbol	Conditions		Values	Linit	
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
		$V_{GS} = 0V$, $I_D = 1mA$				
Drain - Source breakdown voltage	V _{(BR)DSS}	$T_{vj} = 25^{\circ}C$	650	-	-	V
voltago		T _{vj} = -55°C	650	-	-	
		$V_{GS} = 0V, V_{DS} = 650V$				
Zero Gate voltage Drain current	I _{DSS}	$T_{vj} = 25^{\circ}C$	-	1	10	μΑ
Diam current		T _{vj} = 150°C	-	2	-	
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +22V, \ V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I _{GSS-}	$V_{GS} = -4V$, $V_{DS} = 0V$	ı	ı	-100	nA
Gate threshold voltage	V _{GS (th)}	$V_{DS} = 10V, I_{D} = 13.3mA$	2.7	-	5.6	V
		$V_{GS} = 18V, I_D = 27A$				
Static Drain - Source on - state resistance	R _{DS(on)} *5	$T_{vj} = 25^{\circ}C$	-	30	39	mΩ
on state resistance		T _{vj} = 150°C	-	43	-	
Gate input resistance	R_{G}	f = 1MHz, open drain	-	7	-	Ω

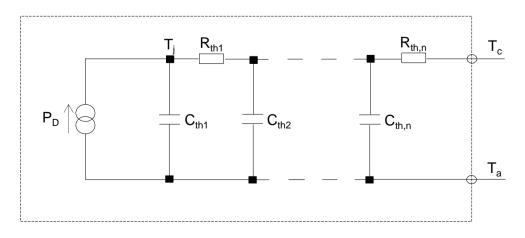
●Thermal resistance

Parameter	Symbol	Values			Unit
r atametet		Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R_{thJC}	-	0.44	0.57	K/W

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	2.56×10 ⁻²	
R _{th2}	1.95×10 ⁻¹	K/W
R _{th3}	2.20×10 ⁻¹	

Symbol	Value	Unit
C_{th1}	1.39×10 ⁻³	
C_{th2}	1.00×10 ⁻²	Ws/K
C _{th3}	3.57×10 ⁻²	



ullet Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

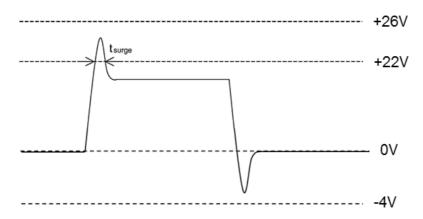
Parameter	Symbol Conditions	Values			Unit	
- Farameter		Cortaitions	Min.	Тур.	Max.	Offic
Transconductance	g_{fs}^{*5}	$V_{DS} = 10V, I_{D} = 27A$	-	9.4	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	1526	-	
Output capacitance	C _{oss}	V _{DS} = 500V	1	89	-	pF
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	42	-	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V \text{ to } 300V$	1	230	1	pF
Total Gate charge	Qg *5	$V_{DS} = 300V$ $I_{D} = 27A$	ı	104	ı	
Gate - Source charge	Q _{gs} *5	$V_{GS} = 18V$	ı	19	-	nC
Gate - Drain charge	Q _{gd} *5	See Fig. 1-1.	-	55	-	
Turn - on delay time	t _{d(on)} *5	$V_{DS} = 400V$ $I_{D} = 40A$	ı	6	-	
Rise time	t _r *5	$V_{GS} = 0V/+18V$	-	26	-	no
Turn - off delay time	t _{d(off)} *5	$R_G = 0\Omega, L = 750\mu H$ $L_{\sigma} = 50 nH, C_{\sigma} = 10 pF$	ı	25	-	ns
Fall time	t _f *5	See Fig. 2-1, 2-2, 2-3.	-	25	-	
Turn - on switching loss	E _{on} *5	E _{on} includes diode reverse recovery.	-	203	-	11.1
Turn - off switching loss	E _{off} *5		-	175	-	μJ

●Body diode electrical characteristics (Source-Drain) (T_{vj} = 25°C unless otherwise specified)

Parameter	Symbol	Conditions		Values	Unit	
raiailletei	Symbol	Coriditions	Min.	Тур.	Max.	Offic
Body diode continuous, forward current	I _S *1	T _c = 25°C	ı	1	70	А
Body diode direct current, pulsed	I _{SM} *2	11 _c = 25 0	ı	ı	175	А
Forward voltage	V _{SD} *5	$V_{GS} = 0V, I_{S} = 27A$	ı	3.2	ı	V
Reverse recovery time	t _{rr} *5	$I_F = 27A$ $V_R = 400V$	ı	28	ı	ns
Reverse recovery charge	Q _{rr} *5	di/dt = 2500A/µs	ı	702	ı	nC
Peak reverse recovery current	: I _{rrm} *5	$L_{\sigma} = 50$ nH, $C_{\sigma} = 10$ pF See Fig. 3-1, 3-2.	-	40	-	А

^{*1} Limited by maximum $T_{\nu j}$ and for Max. R_{thJC} .

^{*3} Example of acceptable V_{GS} waveform



Please note especially when using driver source that $V_{\text{GSS_surge}}$ must be in the range of absolute maximum rating.

*5 Pulsed

^{*2} PW \leq 10 μ s, Duty cycle \leq 1%

^{*4} Please be advised not to use SiC-MOSFETs with V_{GS} below 13V as doing so may cause thermal runaway.

Fig.1 Power Dissipation Derating Curve

300
250
4. 200
150
50
0
25 75 125 175
Case Temperature : T_C [°C]

1000 Operation in this area is limited by R_{DS(on)} 100 Drain Current: I_D [A] PW = 1µs' 10 PW = 10µs PW = 100µs PW = 1ms PW = 10ms 1 $T_c = 25^{\circ}C$ Single Pulse *Calculation(PW≤10µs) 0.1 0.1 10 100 1000 Drain - Source Voltage : V_{DS} [V]

Fig.2 Maximum Safe Operating Area

Fig.3 Typical Transient Thermal Impedance vs. Pulse Width

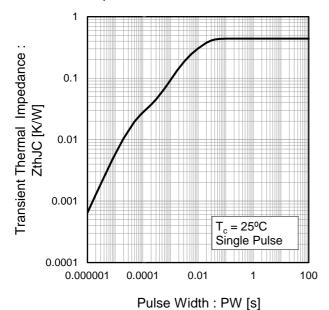


Fig.4 Typical Output Characteristics(I)

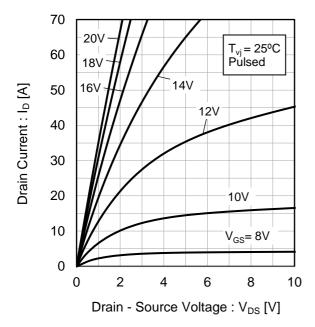


Fig.5 Typical Output Characteristics(II)

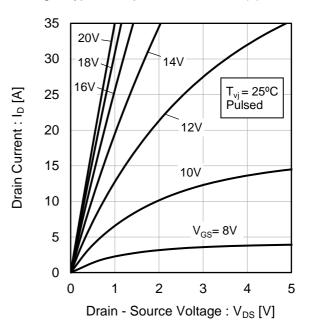
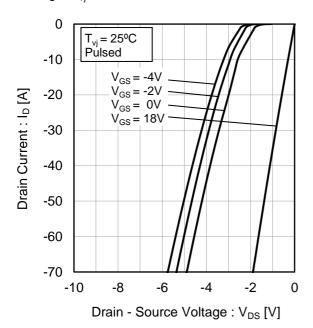
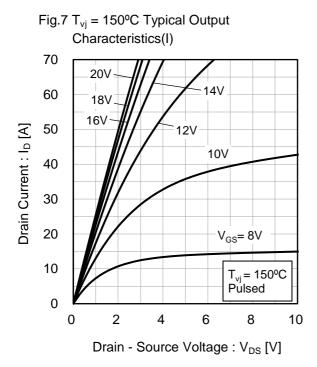


Fig.6 T_{vj} = 25°C 3rd Quadrant Characteristics





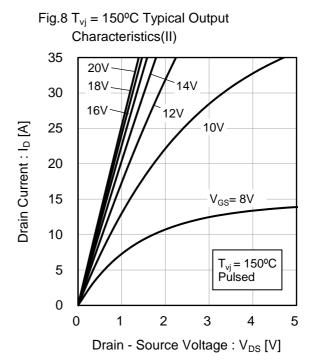


Fig.9 $T_{vj} = 150$ °C 3rd Quadrant Characteristics

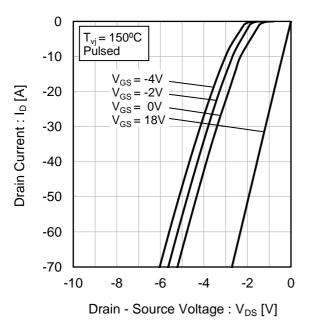


Fig.10 Body Diode Forward Voltage vs. Gate - Source Voltage

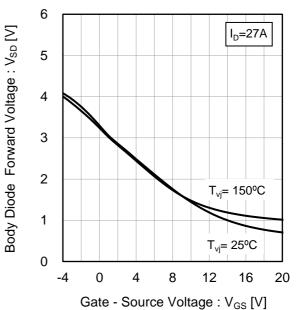


Fig.11 Typical Transfer Characteristics (I)

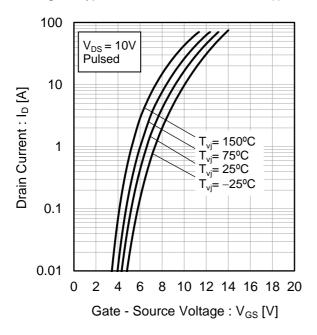


Fig.12 Typical Transfer Characteristics (II)

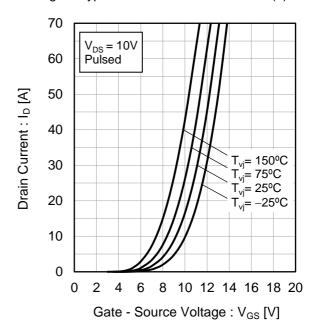


Fig.13 Gate Threshold Voltage vs. Virtual Junction Temperature

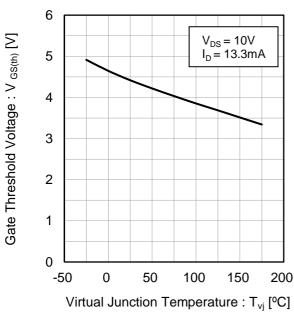


Fig.14 Transconductance vs. Drain Current

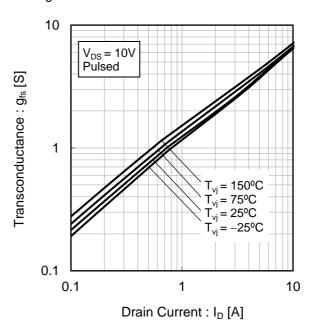


Fig.15 Static Drain - Source On - State Resistance vs. Gate - Source Voltage 0.12 $T_{vi} = 25^{\circ}C$ Púlsed Static Drain - Source On-State 0.10 Resistance : $R_{DS(on)} \left[\Omega \right]$ I_D= 47A 0.08 0.06 I_D= 27A 0.04 $I_D = -27A$ 0.02 0.00 8 10 12 16 18 20 22 Gate - Source Voltage : V_{GS} [V]

Resistance vs. Virtual Junction Temperature 0.06 $V_{GS} = 18V$ Pulsed Static Drain - Source On-State 0.05 $I_D = 47A$ $I_D = 27A$ $I_D = -27A$ 0.01 0.00 0 50 100 200 -50 150

Virtual Junction Temperature : T_{vi} [°C]

Fig.16 Static Drain - Source On - State

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current

0.1

T_{vj} = 150°C

T_{vj} = 125°C

T_{vj} = 75°C

T_{vj} = 25°C

T_{vj} = -25°C

T_{vj} = -25°C

T_{vj} = -25°C

T_{vj} = -25°C

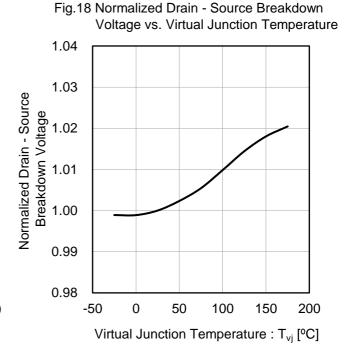


Fig.19 Typical Capacitance vs. Drain - Source Voltage 10000 C_{iss} 1000 Capacitance: C [pF] C_{oss} 100 10 $T_{vj} = 25^{\circ}C$ f = 1MHz $V_{GS} = 0V$ 1 0.1 1 10 100 1000 Drain - Source Voltage : V_{DS} [V]

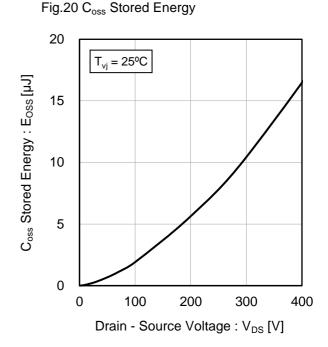
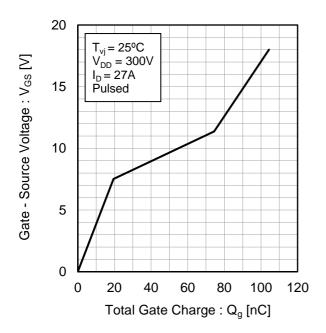
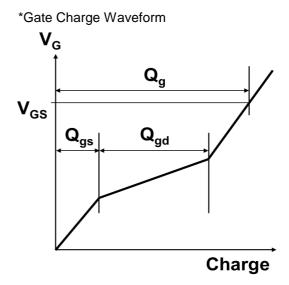
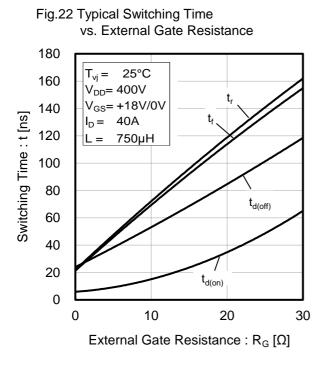


Fig.21 Dynamic Input Characteristics



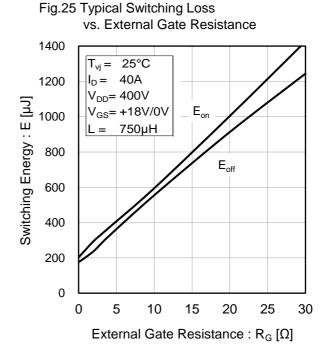




vs. Drain - Source Voltage 400 $T_{vj} = 25^{\circ}C$ 350 $I_D = 40A$ V_{GS}= +18V/0V Switching Energy : E [µJ] 300 $R_G = 0\Omega$ $L = 750 \mu H$ 250 200 150 $\mathsf{E}_{\mathsf{off}}$ 100 50 E_{on} 0 100 200 300 400 500 Drain - Source Voltage: V_{DS} [V]

Fig.23 Typical Switching Loss

Fig.24 Typical Switching Loss vs. Drain Current 1200 25°C $T_{vj} =$ $V_{DD} = 400V$ 1000 $V_{GS} = +18V/0V$ Switching Energy: E [µJ] $R_G = 0\Omega$ 800 $L = 750 \mu H$ 600 400 Eon 200 $\mathsf{E}_{\mathsf{off}}$ 0 30 40 0 10 20 50 70 80 Drain Current : I_D [A]



Measurement circuits and waveforms

Fig.1-1 Gate Charge Measurement Circuit

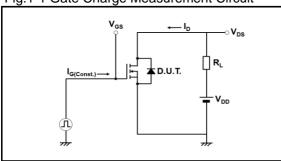


Fig.2-1 Switching Characteristics Measurement Circuit

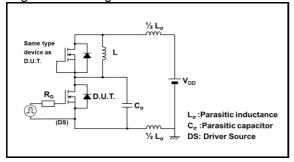


Fig.2-2 Waveforms for Switching Time

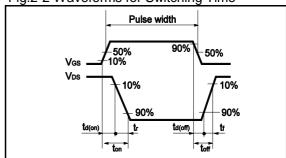


Fig.2-3 Waveforms for Switching Energy Loss

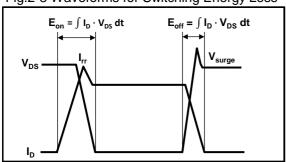


Fig.3-1 Reverse Recovery Time Measurement Circuit

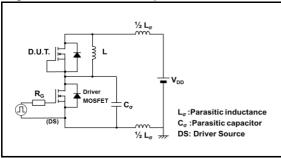
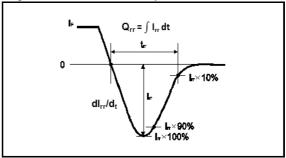
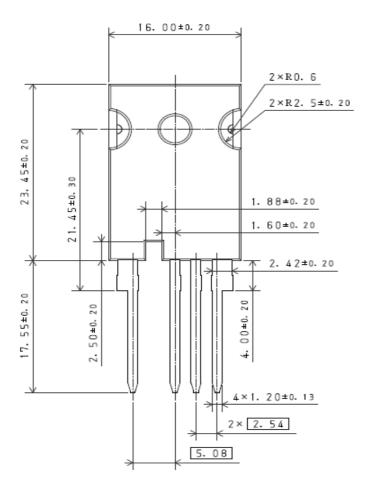
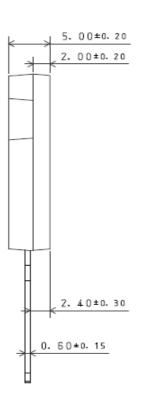


Fig.3-2 Reverse Recovery Waveform

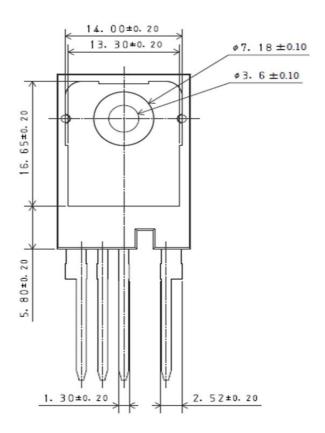


●Package Dimensions



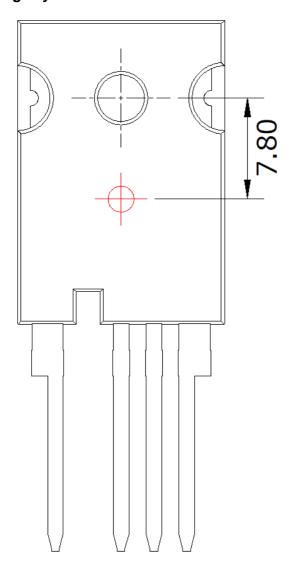


Unit: mm



Unit: mm

●Die Bonding Layout





- •Front view of the packaging.
- •Dimensions are design values.
- •If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm

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